
#### Abstract

Part Number $\quad$ SWITCH TYPE


InPD1012-14 $\quad$ Solid State, InP-HEMT Active RF Switch Die

## DESCRIPTION

The InPD1012-14 is a wideband, reflective SPDT Active RF Switch Die, manufactured using Teledyne's high-speed, lowloss InP HEMT process-making this switch ideal for test and measurement, microwave communications, and radar applications. The InPD1012-14 can also tolerate up to 100 krads of radiation, alowing it to be used in space applications.

## The InPD1012-14 features:

- Broad frequency bandwidth
- Low insertion loss
- Very High linearity
- Wide operating temperature
- Radiation tolerant up to 100 krads
- Very fast switching time of less than 100 ns


## INTERNAL CONSTRUCTION



Electrical Specifications (@25 ${ }^{\circ} \mathrm{C}, \mathrm{V} 1=\mathrm{ON}, \mathrm{V} 2=\mathrm{OFF}$ OR V1 = OFF, V2 = ON, $\mathrm{Z}_{\mathrm{s}}=\mathrm{Z}_{\mathrm{L}}=50 \Omega$ )

| Parameter/Condition | Frequency | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Insertion Loss | $\begin{gathered} \mathrm{DC}{ }^{* *} \\ 10 \mathrm{kHz}-6 \mathrm{GHz} \\ 6-8 \mathrm{GHz} \\ 8-14 \mathrm{GHz} \end{gathered}$ |  | $\begin{aligned} & 2.0 \\ & 1.3 \\ & 1.4 \\ & 1.6 \end{aligned}$ | $\begin{aligned} & 1.5 \\ & 1.6 \\ & 1.8 \end{aligned}$ | dB <br> dB <br> dB <br> dB |
| Isolation | $\begin{gathered} \mathrm{DC}-6 \mathrm{GHz} \\ 6-8 \mathrm{GHz} \\ 8-14 \mathrm{GHz} \end{gathered}$ | $\begin{aligned} & 34 \\ & 32 \\ & 27 \end{aligned}$ | $\begin{aligned} & 36 \\ & 34 \\ & 29 \end{aligned}$ |  | $\begin{aligned} & \mathrm{dB} \\ & \mathrm{~dB} \\ & \mathrm{~dB} \end{aligned}$ |
| Return Loss (active port) | DC - 14 GHz |  | 26 |  | dB |
| Switching Time |  |  | 60 | 100 | ns |
| Operating Power |  |  | 1 | 2 | mW |
| Input 0.1 dB compression point | $\begin{gathered} 100 \mathrm{MHz} \\ 6 \mathrm{GHz} \end{gathered}$ |  | $\begin{gathered} \hline 3.1 \\ 15.7 \end{gathered}$ |  | dBm dBm |
| Input 1dB compression point | $\begin{gathered} 100 \mathrm{MHz} \\ 6 \mathrm{GHz} \end{gathered}$ |  | $\begin{aligned} & \hline 8.6 \\ & 21.1 \end{aligned}$ |  | dBm dBm |
| Input $3^{\text {rd }}$ Order Intercept (IIP3) | 10 GHz |  | 37.5 |  | dBm |

${ }^{* *}$ RF input power ( $20 \mathrm{mV}-200 \mathrm{mV}$ ), Insertion loss increases with higher DC offset, up to 2.5 Vdc max.



Physical Specifications

| Parameter | Min. | Typ. | Max. | Unit |
| :--- | :--- | :--- | :--- | :--- |
| Die Size, Singulated $(\mathbf{x}, \mathbf{y})$ <br> maximum tolerance $= \pm 10 \mu \mathrm{~m}$ | $820 \times 950$ | $830 \times 960$ | $840 \times 970$ | $\mu \mathrm{~m}$ |
| Wafer Thickness | 615 | 625 | 635 | $\mu \mathrm{~m}$ |
| Bump Pitch | 150 |  |  | $\mu \mathrm{~m}$ |
| Bump Height | 50 | 60 | 70 | $\mu \mathrm{~m}$ |
| Bump Diameter |  | 79 |  | $\mu \mathrm{~m}$ |
| UBM Diameter | 65 | 69 | 74 | $\mu \mathrm{~m}$ |

Environmental Specifications

|  |  |  |  |
| :--- | :--- | :--- | :--- |
| Operating Temperature <br> Range | -65 | +125 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature <br> Range | -65 | +125 | ${ }^{\circ} \mathrm{C}$ |
| ESD Sensitivity (HBM) | Class 1 |  |  |
| MSL Sensitivity | TBD |  |  |
| Radiation Tolerance | 100 krads |  |  |

RECOMMENDED OPERATING CONDITIONS

| Parameter | MIN | TYPICAL | MAX | UNIT |
| :--- | :--- | :--- | :--- | :--- |
| Control ON (V1,V2) | -0.3 | 0 | +0.3 | V |
| Control OFF (V1,V2) | -2.0 | -2.5 | -3.0 | V |
| Control Current |  | 200 | 700 | $\mu A$ |

Note: Operation between -0.3 V and -2.0 V is not recommended.

## SWITCH STATES

| V1 | V2 | RF1 | RF2 | STATE |
| :---: | :---: | :---: | :---: | :---: |
| -2.5 V | -2.5 V | OFF | OFF | 1 |
| -2.5 V | 0 V | OFF | ON | 2 |
| 0 V | -2.5 V | ON | OFF | 3 |
| 0 V | 0 V | ON | ON | 4 |

State 1


State 2


State 3

State 4

## Handling Guidelines for Active RF Switches (InP Die Series)

1. Do not drop, throw, or in any way mishandle cartons containing switches.
2. Store switches in a humidity-controlled, shock- and vibration-free environment. Storage temperature range limits are $-65^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$, however, when possible, switches should be stored in an ambient environment. 3. Do not expose switches to humid condition such that condensation may be formed due to sudden drop in temperature. Switches shall be stored in condensation free condition.
3. Active RF switches shall be treated as Electrostatic Discharge (ESD) sensitive and shall be handled accordingly. Always work in ESD protected station and wear wrist strap before handling the device.
4. When removing switches from packs, do so with extreme care. Do not allow the switches to fall onto any hard surface during unpacking. Do not "pour" the switches from the packing. Do not allow switches to fall onto the floor.
5. When transferring switches to a production area after unpacking, do so only in a suitable container, transport the devices in anti-static container, taking care not to drop the switches into the container, or to drop, throw or mishandle the container in any way.
6. Never subject switches to ultrasonic cleaning environment.
7. Unless otherwise specified, do not subject switches to reflow solder temperatures above $245^{\circ} \mathrm{C}, 6$ seconds maximum.
8. If reshipping product do so in original packaging from factory.
9. Switches should not be exposed to any process or environment that exceeds any limits within this guideline or any published specification that applies to the switch.
